June 1998

DS26C32AT/DS26C32AM Quad Differential Line Receiver

sion, while retaining the low power characteristics of CMOS. The DS26C32A has an input sensitivity of 200 mV over the common mode input voltage range of ±7V. The DS26C32A features internal pull-up and pull-down resistors which prevent output oscillation on unused channels.

The DS26C32A provides an enable and disable function common to all four receivers, and features TRI-STATE ® outputs with 6 mA source and sink capability. This product is pin compatible with the DS26LS32A and the AM26LS32.

ENABL

Features

- CMOS design for low power
- ±0.2V sensitivity over input common mode voltage range
- Typical propagation delays: 19 ns
- Typical input hysteresis: 60 mV
- Inputs won't load line when V_{CC} = 0V
- Meets the requirements of EIA standard RS-422
- TRI-STATE outputs for connection to system buses
- Available in Surface Mount
- Mil-Std-883C compliant

OUTPUT C

OUTPUT D

OUTPUT B

OUTPUT A 0087640



N**ational** Semiconductor

General Description

DS26C32AT/DS26C32AM

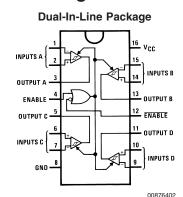
Quad Differential Line Receiver

The DS26C32A is a quad differential line receiver designed

to meet the RS-422, RS-423, and Federal Standards 1020

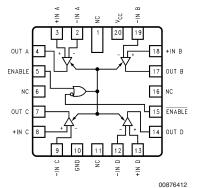
and 1030 for balanced and unbalanced digital data transmis-





Top View Order Number DS26C32ATM or DS26C32ATN See NS Package M16A or N16E For Complete Military Product Specifications, refer to the appropriate SMD or MDS. Order Number DS26C32AME/883, DS26C32AMJ/883 or DS26C32AMW/883 See NS Package E20A, J16A or W16A

20-Lead Ceramic Leadless Chip Carrier



TRI-STATE® is a registered trademark of National Semiconductor Corporation.

Absolute Maximum Ratings (Notes 2,

1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V _{CC})	7V
Common Mode Range (V_{CM})	±14V
Differential Input Voltage (V DIFF)	±14V
Enable Input Voltage (V IN)	7V
Storage Temperature Range (T STG)	–65°C to +150°C
Lead Temperature (Soldering 4 sec.)	260°C
Maximum Power Dissipation at 25°C (N	lote 5)
Ceramic "J" Pkg.	2308 mW
Plastic "N" Pkg.	1645 mW

 SOIC "M" Pkg.
 1190 mW

 Ceramic "E" Pkg.
 2108 mW

 Ceramic "W" Pkg.
 1215 mW

 Maximum Current Per Output
 ±25 mA

This device does not meet 2000V ESD rating. (Note 4)

Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})	4.50	5.50	V
Operating Temperature Range (T_A)			
DS26C32AT	-40	+85	°C
DS26C32AM	-55	+125	°C
Enable Input Rise or Fall Times		500	ns

DC Electrical Characteristics

 $V_{\rm CC}$ = 5V ±10% (unless otherwise specified) (Note 1)

Symbol	Parameter	Condition	Min	Тур	Max	Units	
V_{TH}	Minimum Differential Input Voltage	$V_{OUT} = V_{OH} \text{ or } V_{OL}$ -7V < V_{CM} < +7V	-200	35	+200	mV	
R _{IN}	Input Resistance	$V_{IN} = -7V, +7V$	DS26C32AT	5.0	6.8	10	kΩ
		(Other Input = GND)	DS26C32AM	4.5	6.8	11	kΩ
I _{IN}	Input Current	V _{IN} = +10V,	DS26C32AT		+1.1	+1.5	mA
		Other Input = GND	DS26C32AM		+1.1	+1.8	mA
		$V_{IN} = -10V,$	DS26C32AT		-2.0	-2.5	mA
		Other Input = GND	DS26C32AM		-2.0	-2.7	mA
V _{OH}	Minimum High Level Output Voltage	$V_{CC} = Min, V_{DIFF} = +1V$ $I_{OUT} = -6.0 \text{ mA}$	$V_{CC} = Min, V_{DIFF} = +1V$ $I_{OUT} = -6.0 \text{ mA}$				V
V _{OL}	Maximum Low Level Output Voltage	$V_{CC} = Max, V_{DIFF} = -1V$ $I_{OUT} = 6.0 \text{ mA}$	$V_{CC} = Max, V_{DIFF} = -1V$			0.3	V
V _{IH}	Minimum Enable High Input Level Voltage						V
V _{IL}	Maximum Enable Low Input Level Voltage					0.8	V
l _{oz}	Maximum TRI-STATE® Output Leakage Current	$V_{OUT} = V_{CC} \text{ or GND},$ ENABLE = $V_{IL},$ ENABLE = V_{IH}		±0.5	±5.0	μΑ	
I _I	Maximum Enable Input Current	$V_{IN} = V_{CC} \text{ or } GND$				±1.0	μA
I _{cc}	Quiescent Power	V _{CC} = Max,	DS26C32AT		16	23	mA
	Supply Current	$V_{DIF} = +1V$	DS26C32AM		16	25	mA
V _{HYST}	Input Hysteresis	V _{CM} = 0V			60		mV

AC Electrical Characteristics

 $V_{CC} = 5V \pm 10\%$ (Note 3)

Symbol	Parameter	Conditions	Min	Тур	Мах		Units
					DS26C32AT	DS26C32AM	
t _{PLH} ,	Propagation Delay	C _L = 50 pF					
t _{PHL}	Input to Output	$V_{DIFF} = 2.5V$	10	19	30	35	ns
		$V_{CM} = 0V$					

AC Electrical Characteristics (Continued)

 $V_{CC} = 5V \pm 10\%$ (Note 3)

Symbol	Parameter	Conditions	Min	Тур	Max		Units
					DS26C32AT	DS26C32AM	1
t _{RISE} ,	Output Rise and	C _L = 50 pF					
t _{FALL}	Fall Times	$V_{DIFF} = 2.5V$		4	9	9	ns
		$V_{CM} = 0V$					
t _{PLZ} ,	Propagation Delay	C _L = 50 pF					
t _{PHZ}	ENABLE to Output	$R_L = 1000\Omega$		13	22	29	ns
		$V_{DIFF} = 2.5V$					
t _{PZL} ,	Propagation Delay	C _L = 50 pF					
t _{PZH}	ENABLE to Output	$R_L = 1000\Omega$		13	23	29	ns
		$V_{DIFF} = 2.5V$					

Note 1: Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, all voltages are referenced to ground.

Note 3: Unless otherwise specified, Min/Max limits apply over recommended operating conditions. All typicals are given for V_{CC} = 5V and T_A = 25°C.

Note 4: ESD Rating: HBM (1.5 k Ω , 100 pF)

Inputs ≥2000V

All other pins ${\geq}1000V$

EIAJ (0Ω, 200 pF) ≥350V

Note 5: Ratings apply to ambient temperature at 25°C. Above this temperature derate N Package 13.16 mW/°C, J Package 15.38 mW/°C, M Package 9.52 mW/°C, E Package 12.04 mW/°C, and W package 6.94 mW/°C.

Comparison Table of Switching Characteristics into "LS-Type" Load (Figures 4, 5, 6) (Note 6)

Symbol	Parameter Conditions DS26C32A		DS26LS32A	Units	
			Тур	Тур	
t _{PLH}	Input to Output	C _L = 15 pF	17	23	ns
t _{PHL}			19	23	ns
t _{LZ}	ENABLE to Output	C _L = 5 pF	13	15	ns
t _{HZ}			12	20	ns
t _{ZL}	ENABLE to Output	C _L = 15 pF	13	14	ns
t _{zH}			13	15	ns

Note 6: This table is provided for comparison purposes only. The values in this table for the DS26C32A reflect the performance of the device, but are not tested or guaranteed.

Test and Switching Waveforms

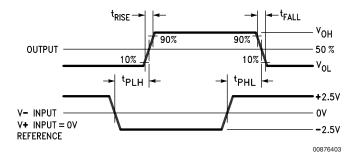
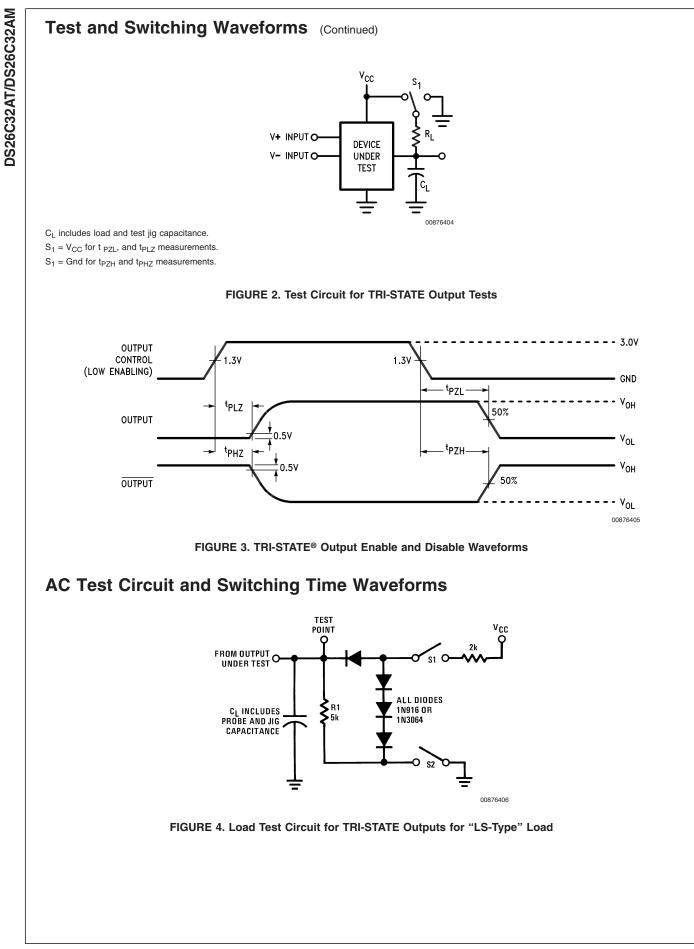


FIGURE 1. Propagation Delay



AC Test Circuit and Switching Time Waveforms (Continued)

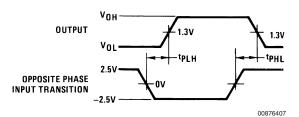
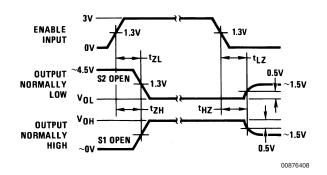


FIGURE 5. Propagation Delay for "LS-Type" Load (Notes 7, 9)





Note 7: Diagram shown for ENABLE low.

Note 8: S1 and S2 of load circuit are closed except where shown.

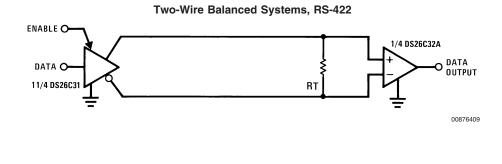
Note 9: Pulse generator for all pulses: Rate \leq 1.0 MHz; Z_O = 50\Omega; t_r \leq 15 ns; t $_f \leq$ 6.0 ns.

Truth Table

ENABLE	ENABLE	Input	Output
L	Н	Х	Z
All Other		$V_{ID} \ge V_{TH}$ (Max)	Н
Combinations of		$V_{ID} \leq V_{TH}$ (Min)	L
Enable Inputs		Open	Н

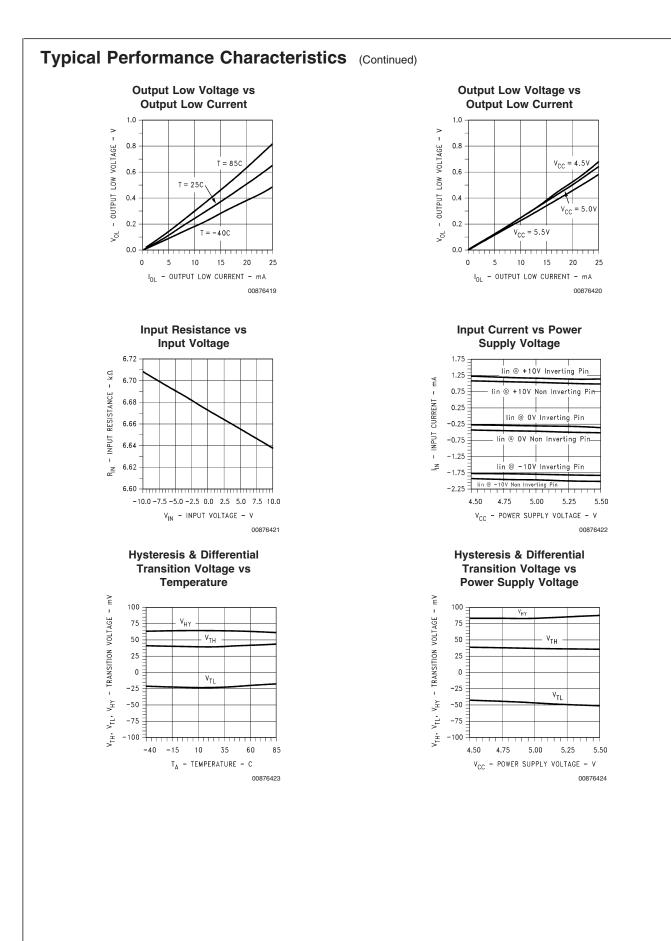
Z = TRI-STATE

Typical Applications

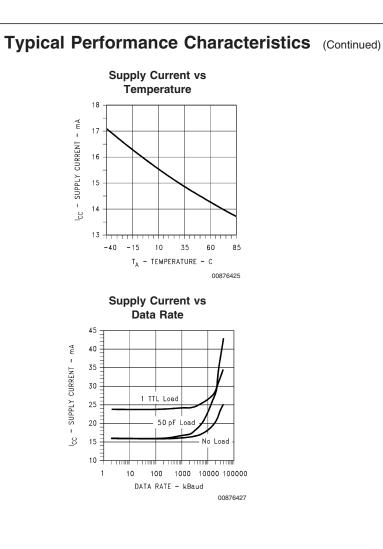


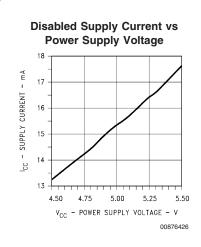


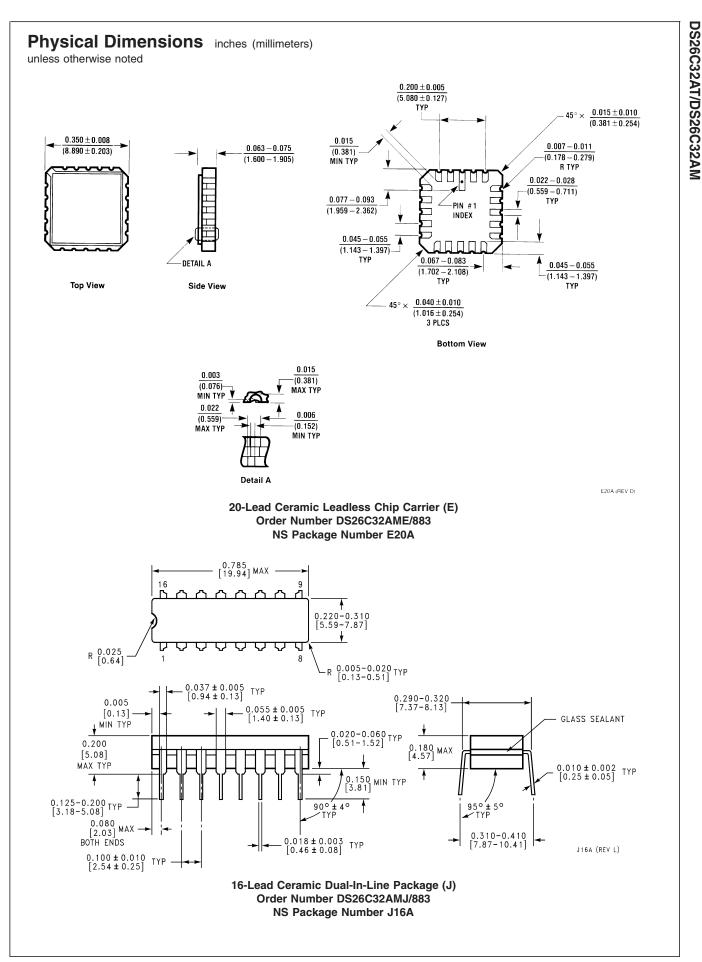
Typical Performance Characteristics Differential Propagation Delay Differential Propagation Delay vs Temperature vs Power Supply Voltage su t_{PHLD} - DIFFERENTIAL PROPAGATION DELAY - ns t_{phld} - Differential propagation delay -22 22 21 21 20 20 PHLD t_{PHLD} 19 19 18 18 t_{PLHD} t_{PLHD} 17 17 16 16 15 15 14 14 tpLHD, t tpLHD, t -40 -15 10 35 60 85 4.50 4.75 5.00 5.25 5.50 $V_{\rm CC}$ - POWER SUPPLY VOLTAGE - V T_A - TEMPERATURE - C 00876414 00876413 **Differential Skew vs Differential Skew vs Power** Temperature **Supply Voltage** 2.00 2.00 - ns - ns DIFFERENTIAL SKEW 1.75 DIFFERENTIAL SKEW 1.75 1.50 1.50 1.25 1.25 tskD tskD 1.00 1.00 -40 -15 10 35 60 85 4.50 4.75 5.00 5.25 5.50 T_A - TEMPERATURE - C V_{CC} - POWER SUPPLY VOLTAGE - V 00876415 00876416 **Output High Voltage vs Output High Voltage vs Output High Current** Output High Current 5.5 5.5 V_{OH} - OUTPUT HIGH VOLTAGE - V - OUTPUT HIGH VOLTAGE - V V_{CC} = 5.5V 5.0 5.0 V_{CC} = 5.0V T = -40C4.5 4.5 T = 250 $V_{CC} = 4.5 V$ T = 850 4.0 4.0 $^{\mathsf{V}_{\mathsf{OH}}}$ 3.5 3.5 0 5 10 15 20 25 0 5 10 15 20 25 I_{OH} - OUTPUT HIGH VOLTAGE - mA I_{OH} - OUTPUT HIGH CURRENT - mA 00876417 00876418

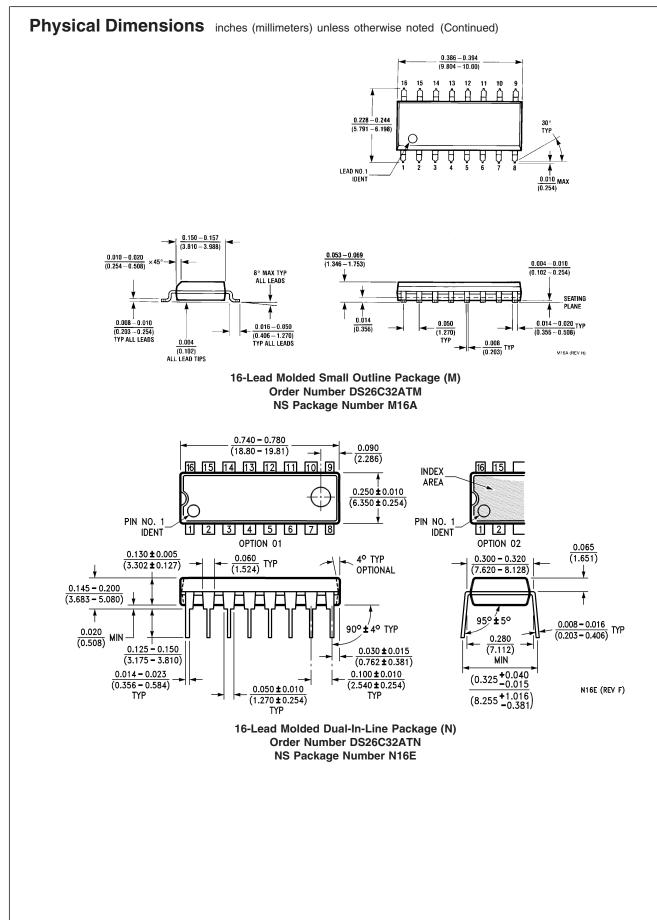


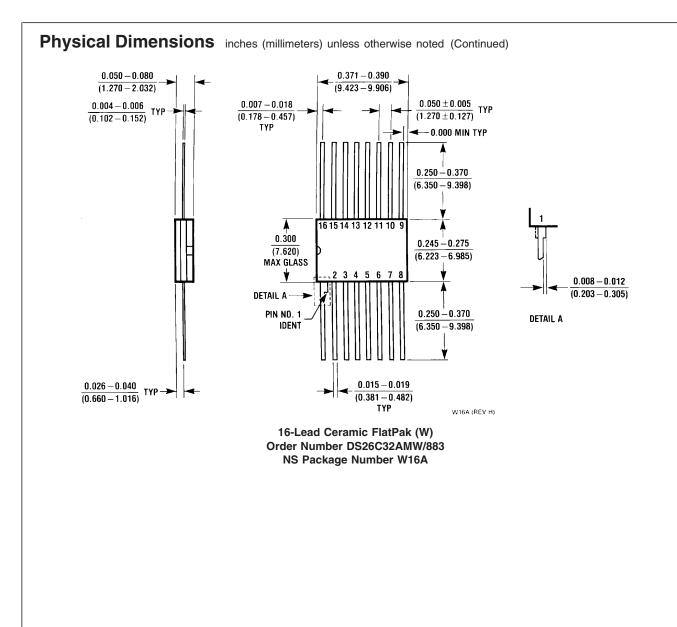
DS26C32AT/DS26C32AM











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